

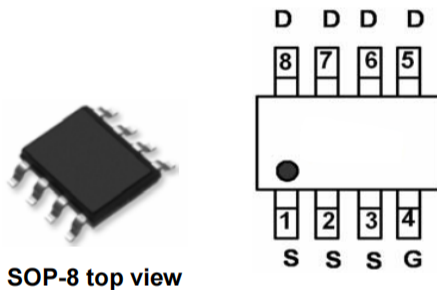
GENERAL FEATURES

- $V_{DS} = 40V$ $I_D = 15A$
- $R_{DS(ON)} < 13m\Omega$ @ $V_{GS} = 10V$

Application

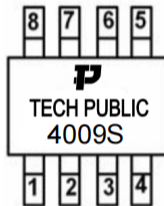
- Battery protection
- Load switch

Package and Pin Configuration

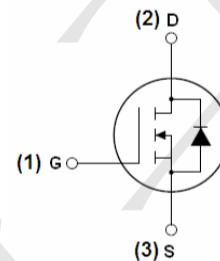


SOP-8 top view

Marking:



Circuit diagram



Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8	A
I_{DM}	Pulsed Drain Current ²	34	A
EAS	Single Pulse Avalanche Energy ³	31	mJ
I_{AS}	Avalanche Current	25	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	65	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	30	$^\circ C/W$

Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.034	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =8A	---	10	13	mΩ
V _{GS(th)}		V _{GS} =4.5V, I _D =6A	---	13	17	
V _{GS(th)}	Gate Threshold Voltage		1.0	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250μA	---	-5.64	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V, T _J =25°C	---	---	1	μA
		V _{DS} =32V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =8A	---	36	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.1	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V, V _{GS} =4.5V, I _D =8A	---	10.7	---	nC
Q _{gs}	Gate-Source Charge		---	3.3	---	
Q _{gd}	Gate-Drain Charge		---	4.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =12V, V _{GS} =10V, R _G =3.3Ω, I _D =6A	---	8.6	---	ns
T _r	Rise Time		---	3.4	---	
T _{d(off)}	Turn-Off Delay Time		---	24.8	---	
T _f	Fall Time		---	2.2	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1314	---	pF
C _{oss}	Output Capacitance		---	120	---	
C _{rss}	Reverse Transfer Capacitance		---	88	---	
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Typical Characteristics

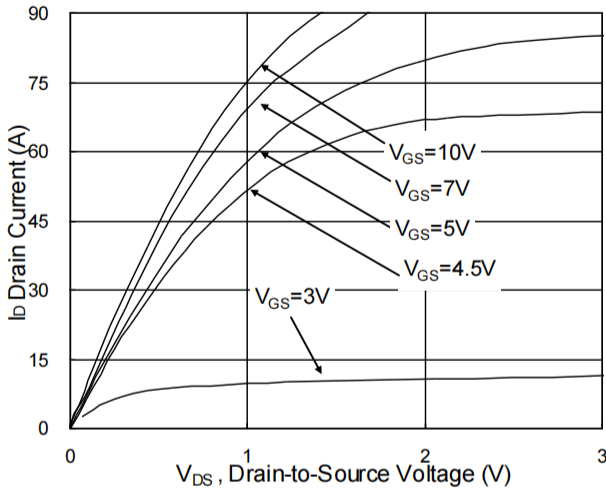


Fig.1 Typical Output Characteristics

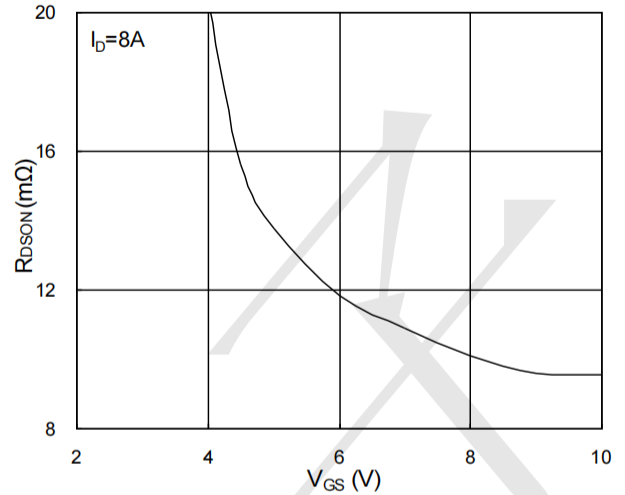


Fig.2 On-Resistance vs. G-S Voltage

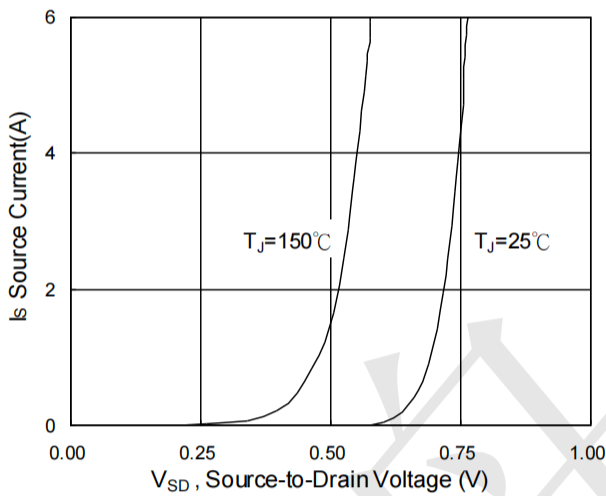


Fig.3 Forward Characteristics of Reverse

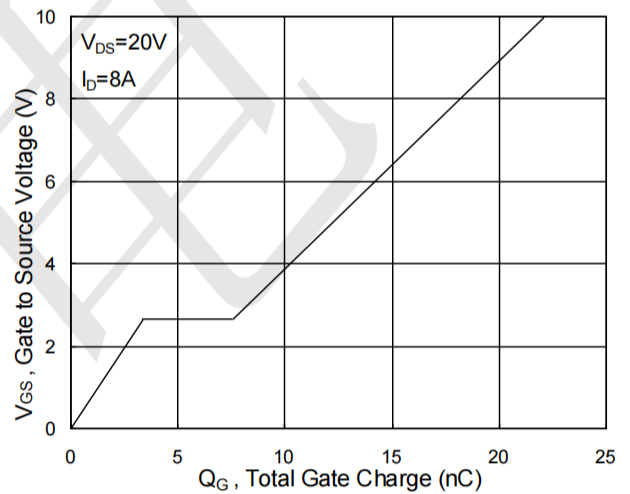


Fig.4 Gate-Charge Characteristics

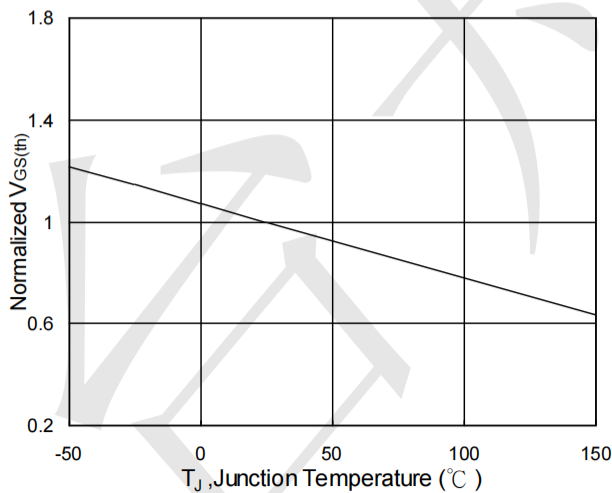


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

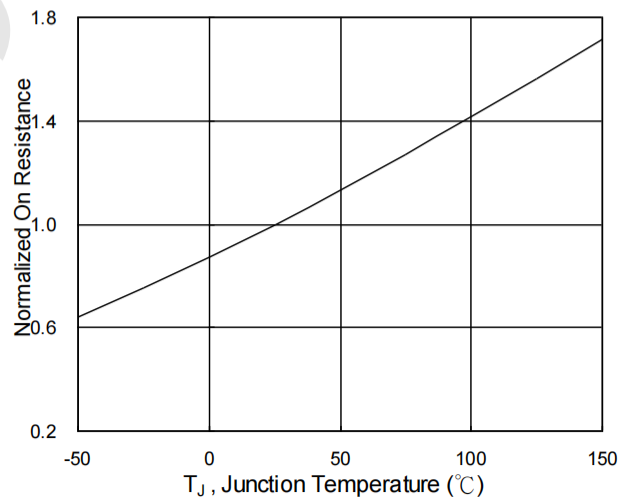


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

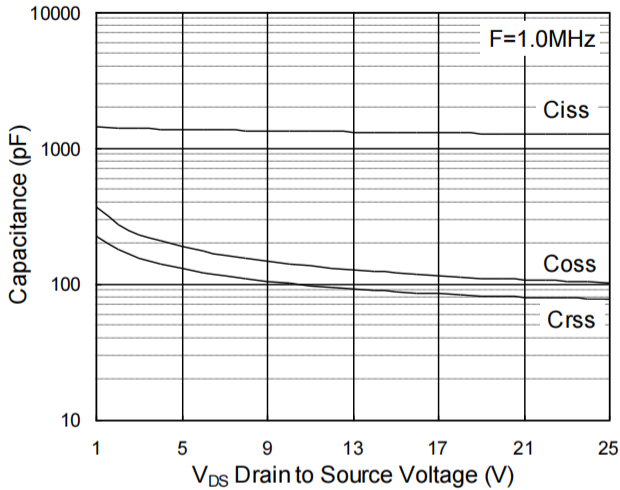


Fig.7 Capacitance

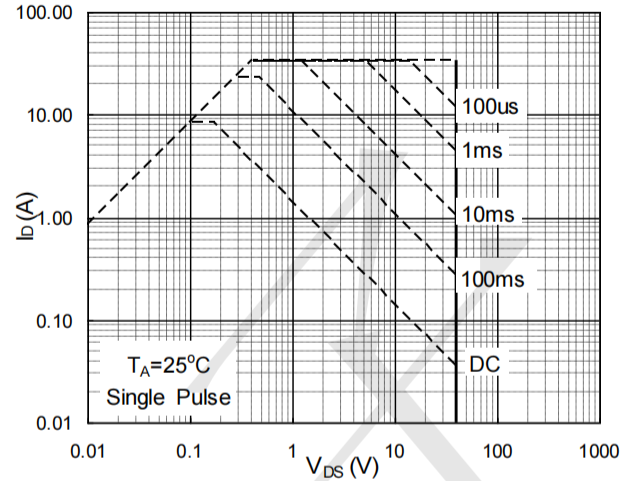


Fig.8 Safe Operating Area

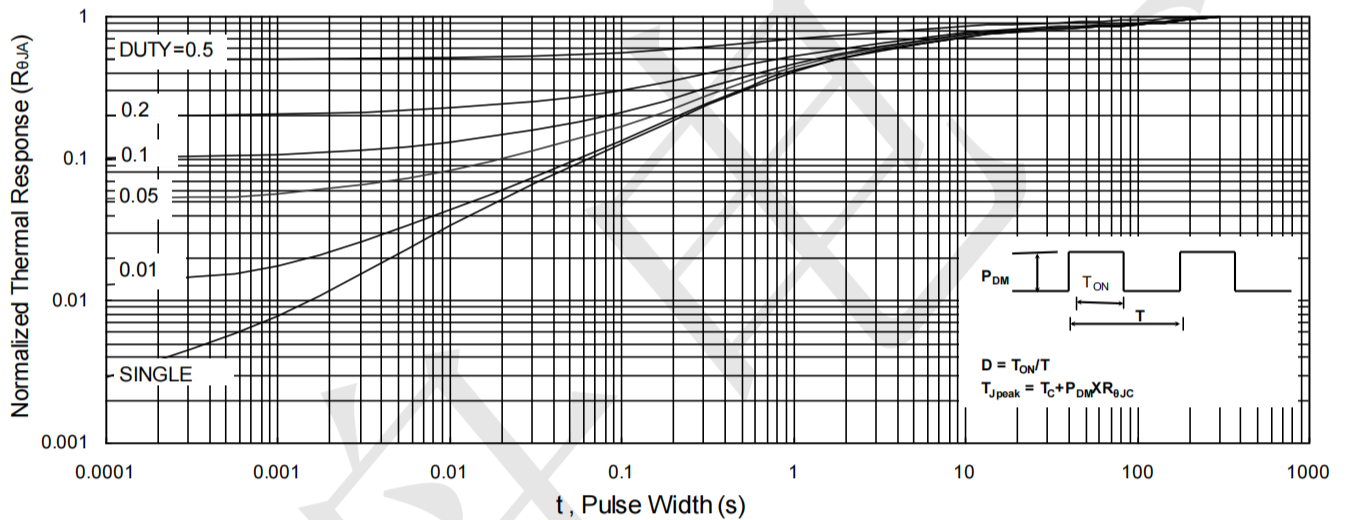


Fig.9 Normalized Maximum Transient Thermal Impedance

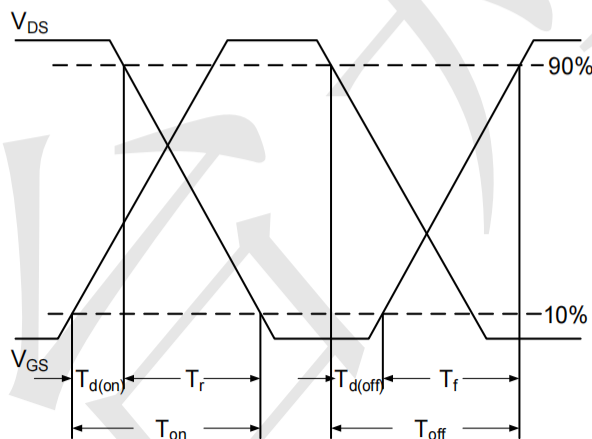


Fig.10 Switching Time Waveform

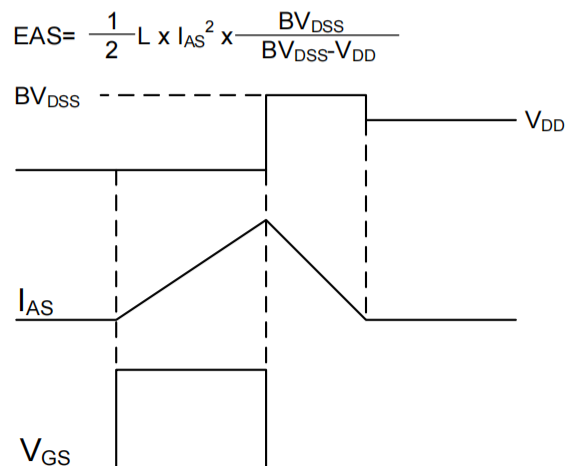
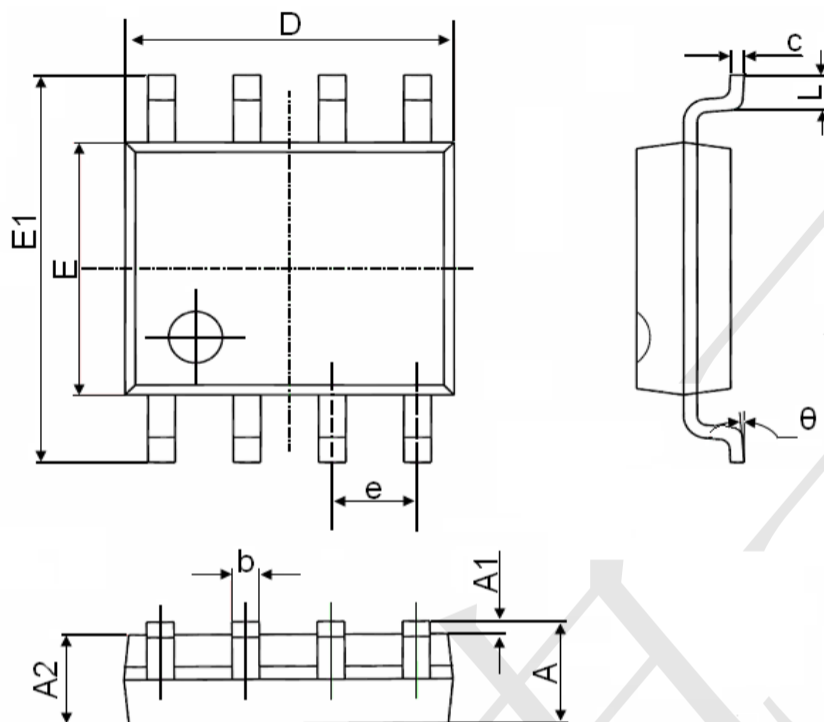


Fig.11 Unclamped Inductive Switching Waveform

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°